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time such as ESD, but also a relatively long time of the millisecond order, can be improved.

FIG. 6 illustrates the high heat conductor layer 6 united with one of the terminal wirings 4A.

Please delete the Abstract of the Disclosure and insert the new Abstract of the Disclosure, attached.

IN THE CLAIMS:

Please cancel claim 1.

Please add the following new claim.

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--6. A semiconductor device, comprising:

- a semiconductor substrate;
- a first insulating film formed on said semiconductor substrate;
- a polysilicon resistor film formed on said first insulating film;
- a second insulating film formed on said resistor film;
- a high heat conductor film consisting of a highly heat-conducting material formed on said second insulating film; and
- a pair of terminal wirings formed on said second insulating film and connected to said resistor film,

wherein a thickness of said second insulating film is thinner than a thickness of said resistor film, and a thickness of said high heat conductor film is thicker than a thickness of said resistor film.